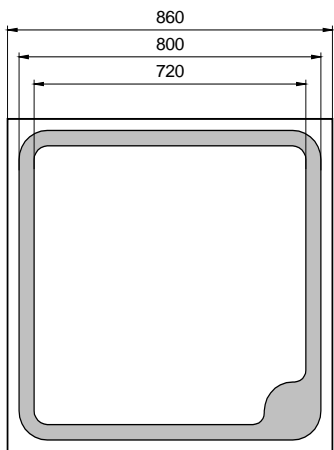


Wavelength range	Type	Technology	Electrodes
Infrared, selective	Integrated filter	AlGaAs/GaAs	P (anode) up

	typ. dimensions (µm)	Description Infrared-selective photodiode with narrow response range (680-770 nm) Applications Optical communications, safety equipment, light barriers
	typ. thickness 300 (±20) µm anode gold alloy, 1.5 µm cathode gold alloy, 0.5 µm	

Miscellaneous Parameters

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Value	Unit
Active area		A	0.62	mm ²
Operating temperature range		T_{amb}	-40 to +125	°C
Storage temperature range		T_{stg}	-40 to +125	°C

Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Reverse voltage ²	$I_R = 10 \mu\text{A}$	V_R	5			V
Dark current	$V_R = 5 \text{ V}$	I_D		40	200	pA
Responsivity at λ_P ¹	$V_R = 0 \text{ V}$	S_λ		0.5		A/W
Peak sensitivity	$V_R = 0 \text{ V}$	λ_P		740		nm
Spectral range at 10 %	$V_R = 0 \text{ V}$	$\lambda_{0.5}$	680		770	nm
Spectral bandwidth at 50%	$V_R = 0 \text{ V}$	$\Delta\lambda_{0.4}$		80		nm
Junction capacitance	$V_R = 0 \text{ V}$	C_J		40		pF
Switching time	$V_R = 5 \text{ V}$	t_r, t_f		15/30		ns

¹Measured on bare chip on TO-18 header

²information only

Labeling

Type	Typ. I_D [pA]	Typ. S_λ [A/W]	Lot N°	Quantity
EPC-740-0.9				

Packing: Chips on adhesive film with wire-bond side on top

*Note: All measurements carried out with *EPIGAP* equipment

